

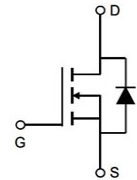
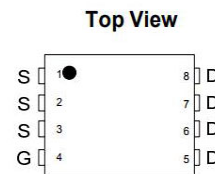
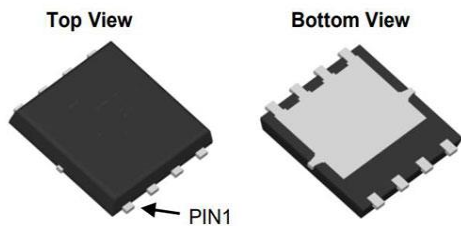
General Description

30V /83A Single N Power MOSFET

 Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=4.5\text{ V}$

Pb-free lead plating; RoHS compliant

V_{DS}	30	V
$R_{DS(on),TYP@V_{GS}=10V}$	3.6	mΩ
$R_{DS(on),TYP@V_{GS}=4.5}$	5.7	mΩ
I_D	83	A



Part ID	Package Type	Marking	Tape and reel information
ACN6354	DFN5x6	6354	3000


 100% UIS Tested
 100% kg tested

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	20	±V
Continuous Drain Current ^A	I_D	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current ^B	I_{DM}	132.8	
Avalanche Current ^G	I_{AR}	26.6	
Repetitive avalanche energy $L=0.1\text{mH}$ ^G	E_{AR}	61.1	mJ
Power Dissipation ^A	P_D	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	13	19	°C/W
Maximum Junction-to-Ambient ^A		Steady State	26	
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	7	12	°C/W

**STATIC PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	I _D = -250uA, V _{GS} = 0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V			1	uA
					5	
I _{GSS}	Gate-Body leakage current	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250μA	1.1	1.7	2.2	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A		3.6	5.2	mΩ
		V _{GS} =4.5V, I _D =20A		5.7	7.4	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		95		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =210V		0.72	1	V
I _S	Maximum Body-Diode Continuous Current				83	A

DYNAMIC PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		1330	1622	pF
C _{oss}	Output Capacitance			360	442	pF
C _{rss}	Reverse Transfer Capacitance			55	65	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz			1.75	Ω

SWITCHING PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A		10		nC
Q _g 4.5V)	Total Gate Charge			5		
Q _{gs}	Gate Source Charge			2.45		
Q _{gd}	Gate Drain Charge			3.5		
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		5.5		ns
t _r	Turn-On Rise Time			4.4		
t _{D(off)}	Turn-Off DelayTime			15.4		
t _f	Turn-Off Fall Time			4.95		
t _{rr}	Body Diode Reverse Recovery Time	I _F =-8A, dI/dt=500A/μs		11		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =18A, dI/dt=500A/μs		17		nC

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

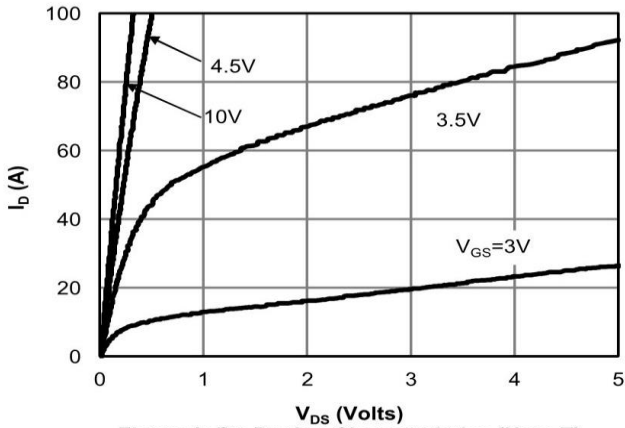


Figure 1: On-Region Characteristics (Note E)

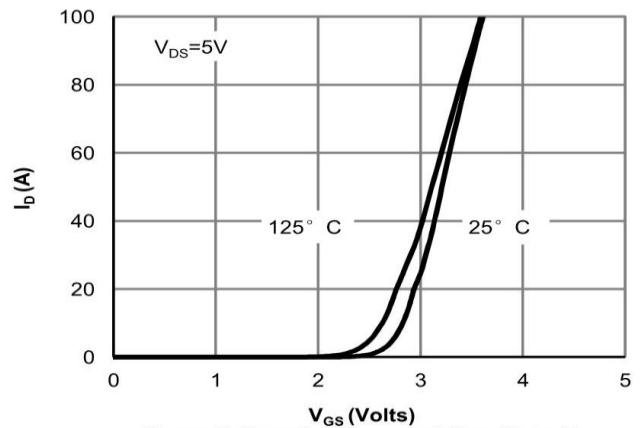


Figure 2: Transfer Characteristics (Note E)

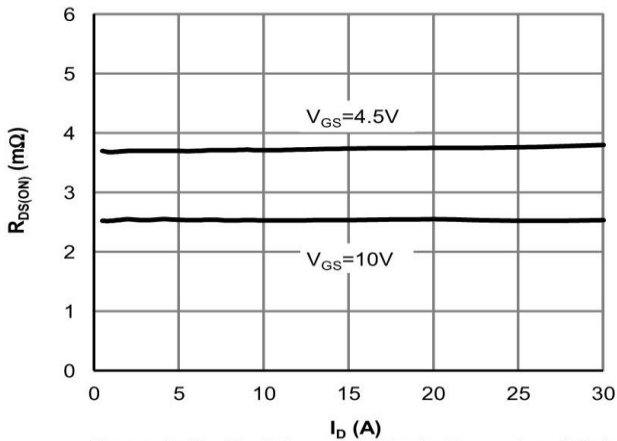


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

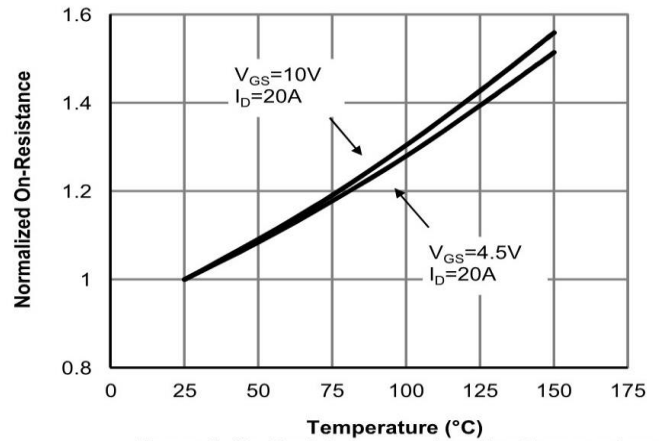


Figure 4: On-Resistance vs. Junction Temperature (Note E)

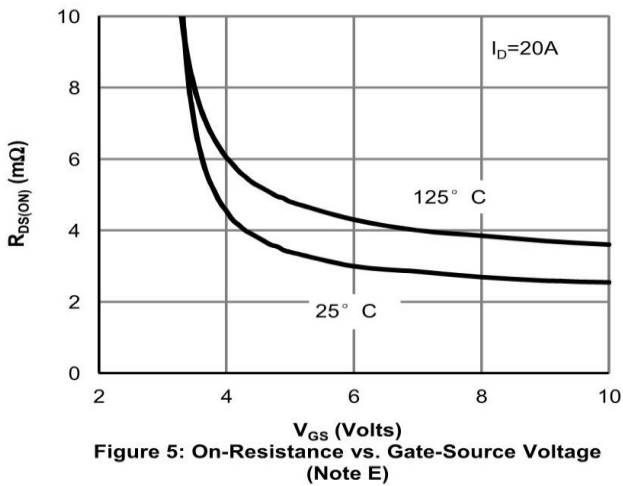


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

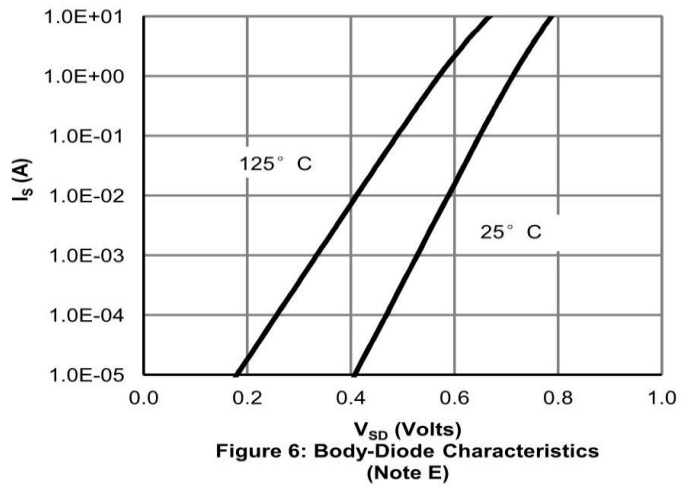


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

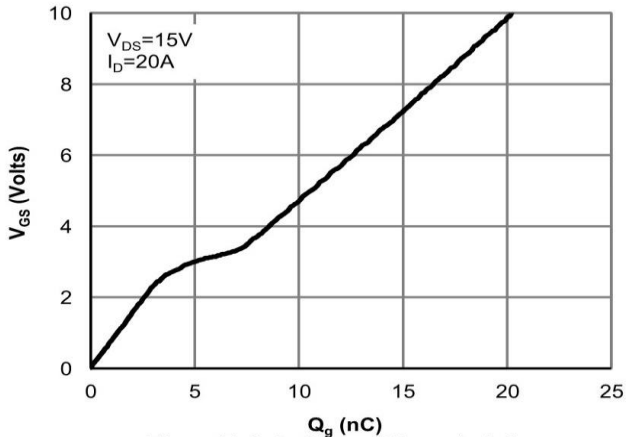


Figure 7: Gate-Charge Characteristics

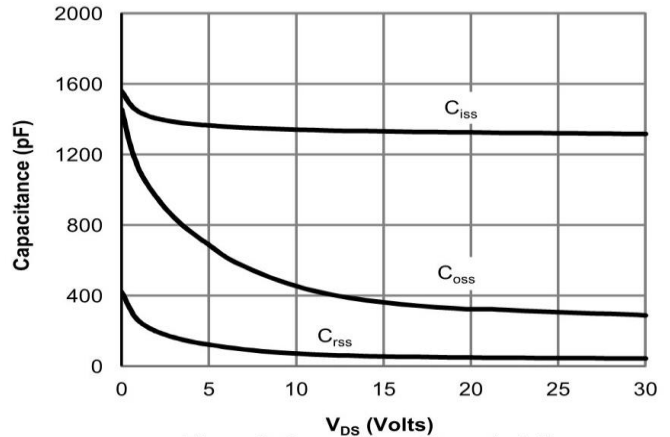


Figure 8: Capacitance Characteristics

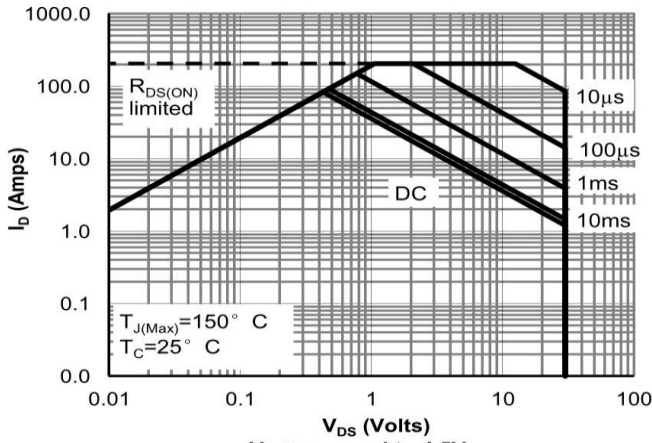


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

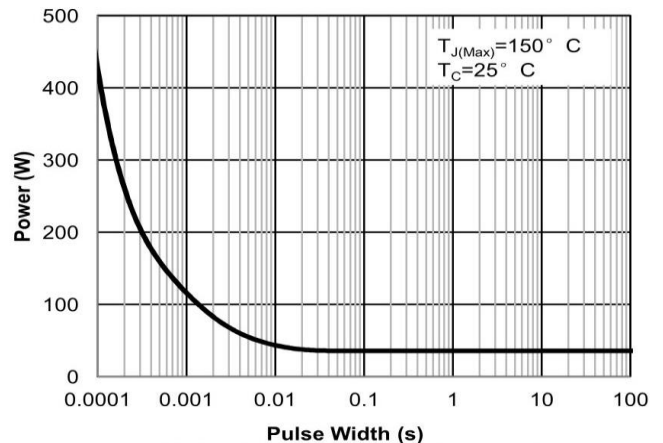


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

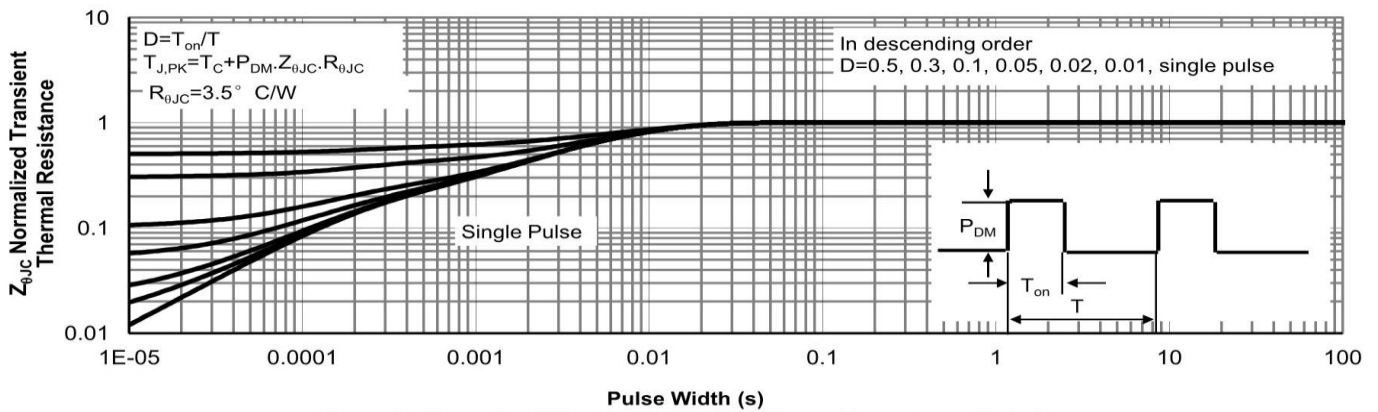


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)